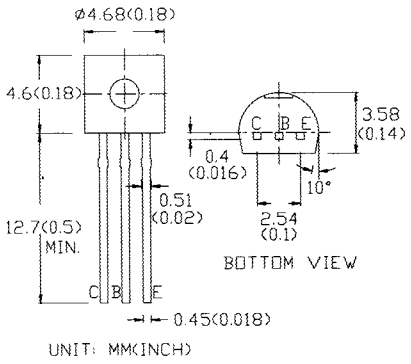
MICRO ELECTRONICS

MPS8599

PNP SILICON TRANSISTOR

TO-92A



DESCRIPTION

MPS8599 is PNP silicon transistor designed for general purpose amplifier applications for audio circuits.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	80V
Collector-Emitter Voltage	VCEO	80V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	200mA
Continuous Power Dissipation	Pd	350mW
Operating & Storage Junction Temperature	Tj,Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LVCEO	80		V	IC=0.5mA	IB=0
Collector-Base Breakdown Voltage	BVCBO	80		V		
Emtter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA	IC=0
Collector Cutoff Current	ICEO		1	μA	VCE=60V	IB=0
Collector Cutoff Current	ICBO		100	nA	VCB=80V	IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=5V	IC=0
D.C. Current Gain	HFE*	100	300		IC=1mA	VCE=5V
		100			IC=10mA	VCE=5V
		75			IC=100mA	VCE=5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=100mA	IB=5mA
			0.3	V	IC=100mA	IB=10mA
Base-Emitter Voltage	VBE		0.8	V	IC=10mA	VCE=5V
Current Gain Bandwidth Product	fT	150		MHz	IC=10mA	VCE=5V
					f=100MHz	
Output Capacitance	Cob		8	pF	VCB=5V	IE=0
					f=1MHz	
Input Capacitance	Cib		30	pF	VEB=0.5V	IC=0
					f=1MHz	

* Pulse test : pulse width <300μS, duty cycle < 2%.

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